

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A semiconductor device, comprising  
a layer fabricated with pulsed radiation ~~annealing~~,  
a layer that can be damaged by said pulsed radiation, said layer that can  
be damaged by said pulsed radiation operatively connected to said layer  
fabricated with pulsed radiation ~~annealing~~, and  
a narrowband reflective coating layer, said narrowband reflective coating  
layer operatively connected to said layer that can be damaged by said pulsed  
radiation, and positioned over said layer that can be damaged by said pulsed  
radiation for reflecting said pulsed radiation and protecting said layer that can be  
damaged by said pulsed radiation.

2. (Original) The semiconductor device of claim 1 wherein said layer that  
can be damaged by said pulsed radiation is low temperature plastic.

3. (Currently Amended) The semiconductor device of claim 1 wherein  
said reflective coating layer is single layer or multiple layers for narrowband ~~or  
broadband~~ reflection.

4. (Currently Amended) The semiconductor device of claim 3 wherein  
said reflective coating layer is a narrow band reflectance coating.

5. (Currently Amended) The semiconductor device of claim 1 wherein  
said layer ~~fabricated with pulsed radiation annealing~~ is fabricated with high  
intensity radiation sources with a short wavelength that will be readily absorbed  
reflective coating layer comprises the materials SiNx and SiO<sub>2</sub>.

6. (Currently Amended) The semiconductor device of claim 5 ~~1~~ wherein said ~~high intensity radiation sources are pulsed UV excimer lasers, frequency doubled NdYAG lasers, UV flashlamps, or X-ray sources~~ reflective coating layer comprises the materials HfOx and SiO<sub>2</sub>.

7. (Currently Amended) The semiconductor device of claim 1 wherein said ~~layer fabricated with pulsed radiation annealing is a silicon film that is crystallized by said pulsed radiation annealing~~ reflective coating layer comprises the materials SiN<sub>x</sub> and SiO<sub>2</sub> that has a high reflectance in the UV, greater than 70% for wavelengths between 300nm and 335nm.

8. (Currently Amended) The semiconductor device of claim 1 wherein said ~~layer fabricated with pulsed radiation annealing is a silicon film that is doped by said pulsed radiation annealing~~ reflective coating layer comprises the materials HfOx and SiO<sub>2</sub> that will give greater than 99% reflection at 308nm.

9. (Currently Amended) The semiconductor device of claim 1 including an insulating layer operatively connected to said layer that can be damaged by said pulsed radiation and operatively connected to said narrowband reflective coating layer for reflecting said pulsed radiation.

10. (Currently Amended) The semiconductor device of claim 1 wherein said layer that can be damaged by said pulsed radiation is low temperature plastic, said reflective coating layer is single layer or multiple layers for narrowband ~~or broadband~~ reflection, and said layer fabricated with pulsed

radiation ~~annealing~~ is a layer that has been fabricated with high intensity radiation sources.

11. (Currently Amended) The semiconductor device of claim 8 1 wherein said ~~high intensity radiation sources are pulsed UV excimer lasers, frequency doubled NdYAG lasers, UV flashlamps, or X-ray sources~~ layer that can be damaged by said pulsed radiation is polyester.

12. (Currently Amended) The semiconductor device of claim 9 1 wherein said reflective coating layer is a narrow band reflectance coating comprising the materials SiNx and SiO<sub>2</sub> that has a high reflectance in the UV, greater than 70% for wavelengths between 300nm and 335nm.

13. (Currently Amended) The semiconductor device of claim ~~10~~ 1 including an insulating layer operatively connected to said layer that can be damaged by said pulsed radiation and wherein said reflective coating layer is a narrow band reflectance coating comprising the materials SiNx and SiO<sub>2</sub> that has a high reflectance in the UV, greater than 70% for wavelengths between 300nm and 335nm for reflecting said pulsed radiation.

Application No.: 10/621,875

AMENDMENTS TO THE DRAWINGS

Enclosed is a letter to the Office Draftsman providing a set of new drawings. The new drawings correct the requirement set out in the Office Action mailed April 2, 2004.